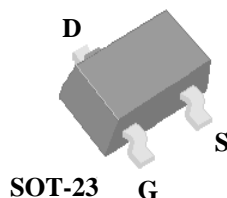




- ▼ Capable of 1.8V gate drive
- ▼ Simple Drive Requirement
- ▼ Surface mount package

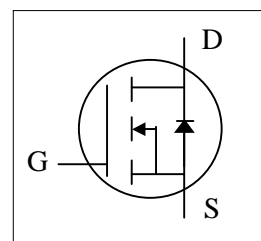


$BV_{DSS}$	20V
$R_{DS(ON)}$	120m $\Omega$
$I_D$	2.2A

## Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-23 package is universally used for all commercial-industrial applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 8$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS}$ @ 4.5V	2.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current <sup>3</sup> , $V_{GS}$ @ 4.5V	1.7	A
$I_{DM}$	Pulsed Drain Current <sup>1,2</sup>	10	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	0.833	W
	Linear Derating Factor	0.006	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-a}$	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 150	$^\circ C/W$



**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.02	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.6A	-	-	120	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A	-	-	150	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.3A	-	-	300	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	0.3	-	1	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	-	2	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±8V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =2.2A	-	7	11	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =16V	-	0.7	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	2.5	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =10V	-	6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	12	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =5V	-	16	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =10Ω	-	4	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	350	560	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =20V	-	55	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	48	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	3.2	4.8	Ω

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =0.7A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>S</sub> =2A, V <sub>GS</sub> =0V,	-	20	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	13	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse width ≤300us , duty cycle ≤2%.
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board , t ≤10sec ; 360 °C/W when mounted on Min. copper pad.

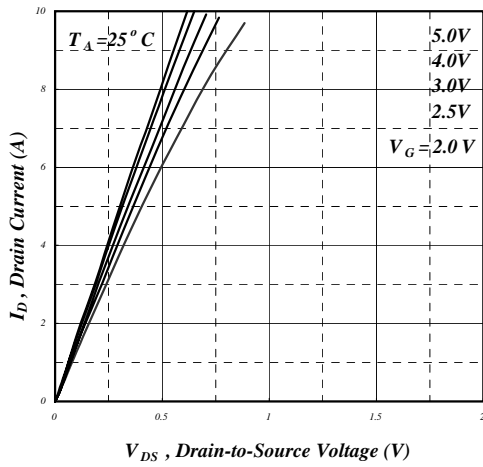


Fig 1. Typical Output Characteristics

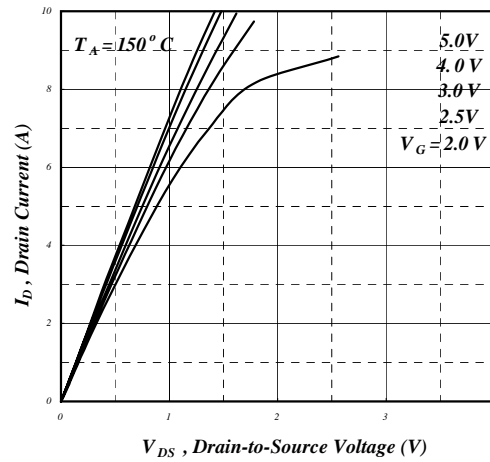


Fig 2. Typical Output Characteristics

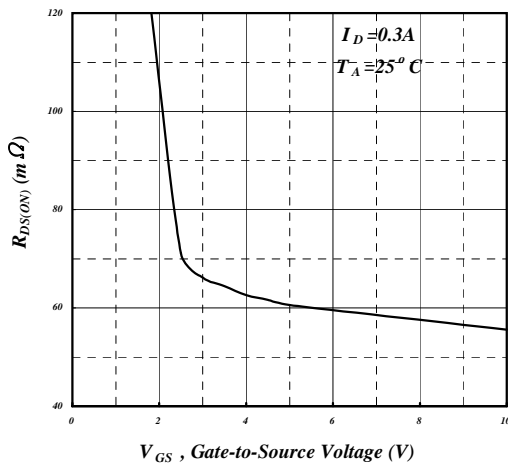


Fig 3. On-Resistance v.s. Gate Voltage

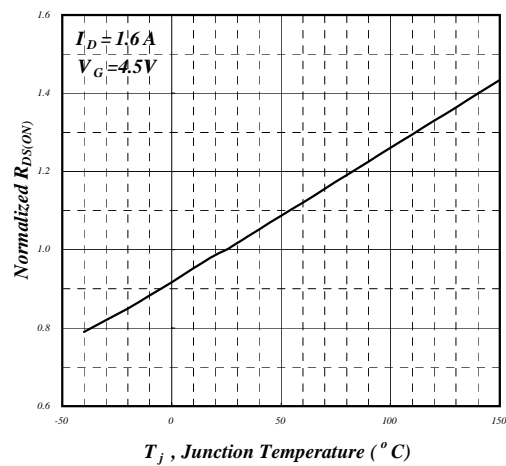


Fig 4. Normalized On-Resistance v.s. Junction Temperature

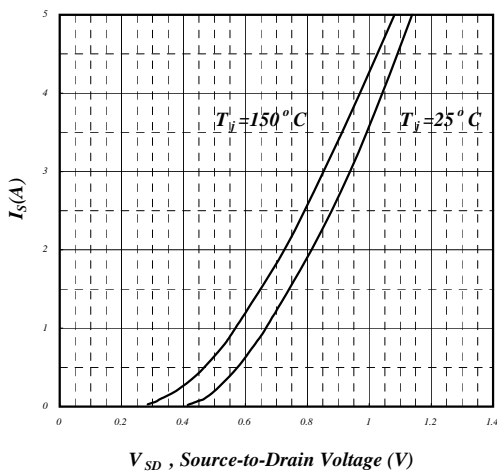


Fig 5. Forward Characteristic of Reverse Diode

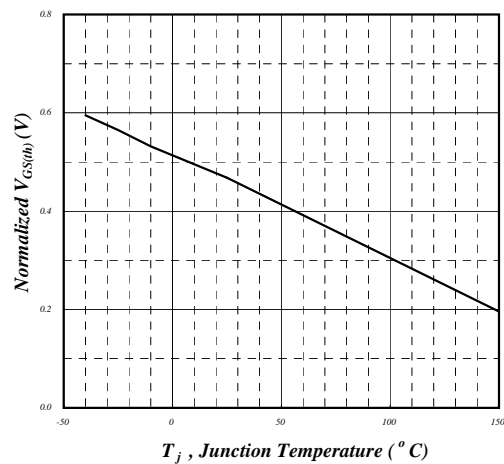


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

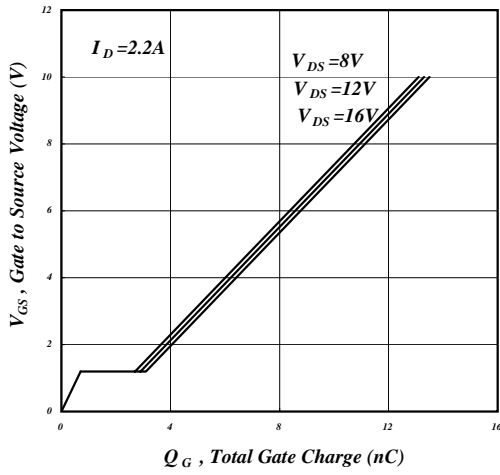


Fig 7. Gate Charge Characteristics

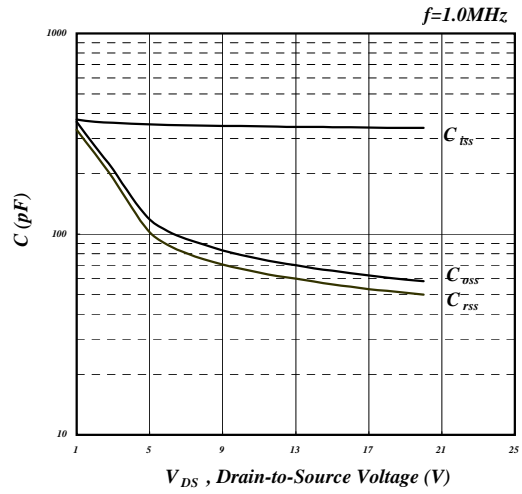


Fig 8. Typical Capacitance Characteristics

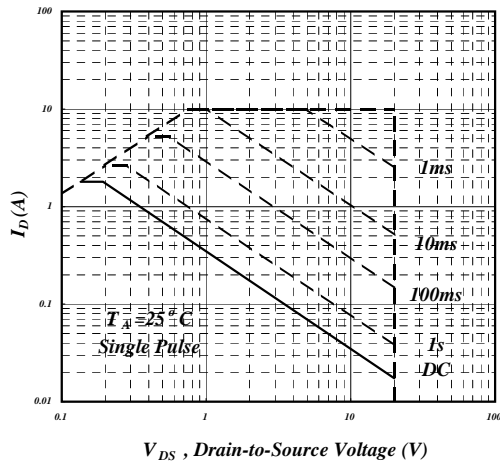


Fig 9. Maximum Safe Operating Area

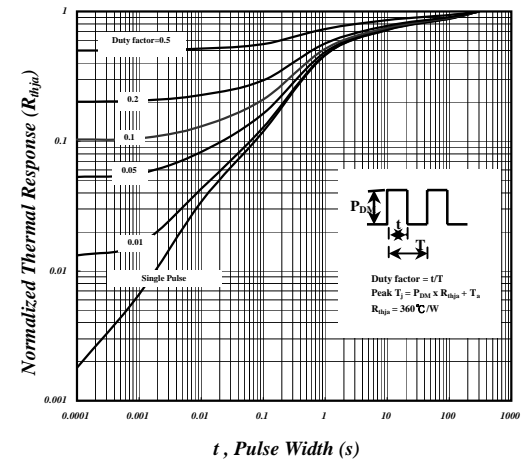


Fig 10. Effective Transient Thermal Impedance

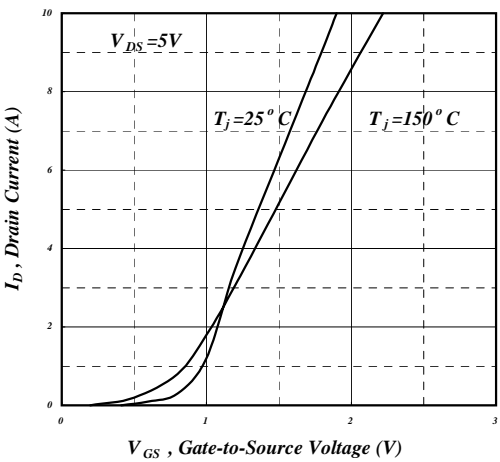


Fig 11. Transfer Characteristics

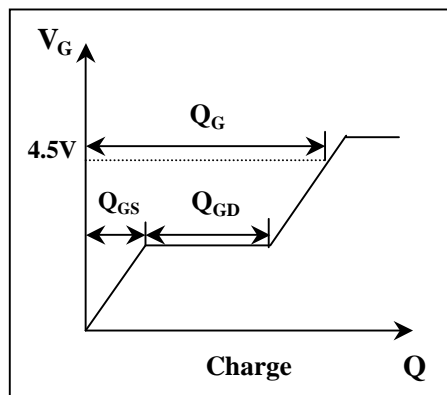
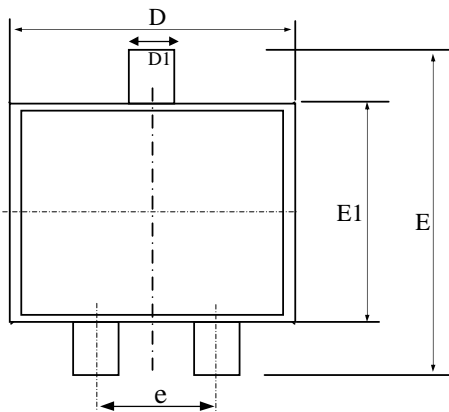


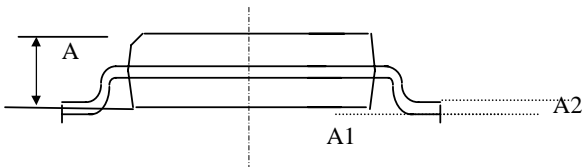
Fig 12. Gate Charge Circuit



### Package Outline : SOT-23



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.00	1.15	1.30
A1	0.00	--	0.10
A2	0.10	0.15	0.25
D1	0.30	0.40	0.50
e	1.70	2.00	2.30
D	2.70	2.90	3.10
E	2.40	2.65	3.00
E1	1.40	1.50	1.80



- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

### Part Marking Information & Packing : SOT-23

